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region (42) being of said first conductivity type, for electrically isolating said second portion of said substrate layer (13) within the substrate (6), wherein said channel stopper region (42) is arranged to extend substantially as an extended channel stopper region (47) in between said second diffusion region (45) and said second buried layer (12), for reducing said second breakdown voltage.

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8. (Amended) A method according to claim 6, further comprising the step of forming by ion-implantation a channel stopper region (42) in said second portion of said substrate layer (13); *B* the channel stopper regions (42) being of said first conductivity type, for electrically isolating said second portion of said substrate layer (13) within the substrate (6) wherein said channel stopper region (42) is formed by ion-implantation as an extended channel stopper region (47) in between said second diffusion region (45) and said second buried layer (12), for reducing said second breakdown voltage.

REMARKS

The foregoing amendments to claims 3-5 and 8, were made solely to avoid filing the claims in the multiple dependent form so as to avoid the additional filing fee.